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July 18, 2005

Time: 9:25 AM PDT  
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To: Commissioner for Patents  
Attn: Responses to Office Actions  
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Alexandria, VA 22313-1450

From: Pamela J. Squyres  
Attorney Docket: MA-108  
Phone: 408-869-2921

FAX NUMBER 571-273-8300

Re: Patent Application of: James Cleeves et al.	Examiner: Ginette Peralta
Serial No.: 10/681,509	Group Art Unit: 2814
Filed: October 7, 2003	Attorney Docket No.: MA-108
Title: Uniform Seeding to Control Grain and Defect Density of Crystallized Silicon for Use in Sub- Micron Thin Film Transistors	

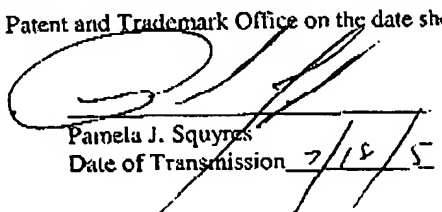
**Document(s) Transmitted:**

- ☐ Response to Restriction Requirement (2 pages)

Total pages of this transmission, including the cover letter: 3

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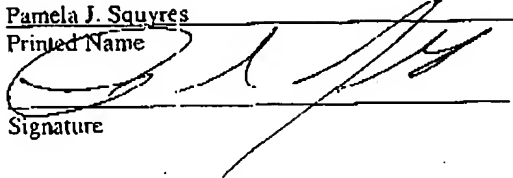
  
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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant(s): James M. Cleeves

Application No.: 10/681,509

Filed: 10/07/03

Title: Uniform Seeding to Control  
Grain and Defect Density of Crystallized  
Silicon for Use in Sub-Micron Thin Film  
Transistors

Attorney Docket No.: MA-108

Group Art Unit: 2814

Examiner: Ginette Peralta

Commissioner for Patents  
PO Box 1450  
Alexandria VA 22313-1450

July 18, 2005

**RESPONSE TO RESTRICTION REQUIREMENT**

To the Commissioner:

In the Restriction Requirement mailed June 29, 2005, Applicants were directed to elect between the claims of Group I (claims 1-5) drawn to a semiconductor die, and the claims of Group II (claims 7-62), drawn to a method for crystallizing a layer. Applicant elects to pursue the method claims of Group II, with traverse.

App. No. 10/681,509

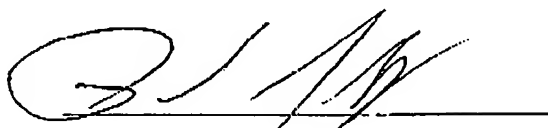
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The Examiner maintains that these inventions are distinct because the product (Group I) could be manufactured by a materially different process that may include implanting the crystallizing agent and annealing or a plasma treatment. Applicants don't dispute that implanting a crystallizing agent and annealing or performing a plasma treatment may form a die having a crystallized silicon layer. There are additional requirements in the invention of Group I, however, relating to adjacent nucleation sites and degree of crystallization. Applicants traverse the requirement for restriction on the grounds that the crystallized layer of the Group I claims, which includes the additional restrictions regarding adjacent nucleation sites and the specified number of grain boundaries, can only be formed using the methods of Group II.

If there are any questions concerning this Response, the Examiner is invited to contact the undersigned agent at (408) 869-2921.

Dated: July 18, 2005

Respectfully submitted,



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